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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/531,442	03/01/2006	Mun-Pyo Hong	YOM-0242	7000
23413 7590 08/07/2007 CANTOR COLBURN, LLP 55 GRIFFIN ROAD SOUTH BLOOMFIELD, CT 06002			EXAMINER POMPEY, RON EVERETT	
			ART UNIT 2812	PAPER NUMBER
			MAIL DATE 08/07/2007	DELIVERY MODE PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

DETAILED ACTION

Claim Rejections - 35 USC § 103

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claims 1-4 and 13-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kim (US 6624871), in view of Morozumi (US 4862237).

Kim discloses the limitations of:

Claim 1. A thin film transistor array panel comprising: a gate wire formed on the substrate and including a gate line (31L, fig. 4A) and a gate electrode (31G, fig. 4A) connected to the gate line; a gate insulating layer (32, fig. 4A) formed on the gate line; a semiconductor layer (33, fig. 4A) formed on the gate insulating layer; a data wire formed on the semiconductor layer and including a data line (35L, fig. 4A) intersecting the gate line, a source electrode (35S, fig. 4A) connected to the data line, and a drain electrode (35D, fig. 4A) located opposite the source electrode with respect to the gate electrode; a pixel electrode (37, fig. 4A) connected to the drain electrode; and an etching assistant pattern (39, fig. 4A) made of the same layer as the semiconductor pattern (the photoresist 39 is the etching assistant pattern over the 31G and semiconductor pattern is the pattern to the left; which is of the same material) and located out of an area (out of the area due to the pattern does not cover the gate line) defined by intersections of the gate line and the data line (col. 4, lns. 58).

Claim 2. The thin film transistor array panel of claim 1, wherein the data wire comprises a lower film of Cr, Mo or Mo ally and an upper film of Al or Al ally (col. 4, Ins. 28-31).

Claim 3. The thin film transistor array panel of claim 2, further comprising a passivation layer (36, fig. 4A) disposed between the data wire and the pixel electrode.

Claim 4. The thin film transistor array panel of claim 3, wherein the semiconductor layer has substantially the same planar shape as the data wire except for a channel portion located between the data line and the drain electrode.

13. The thin film transistor array panel of claim 1, wherein the etching assistant pattern is located outside of a pixel area.

14. The thin film transistor array panel of claim 1, wherein the etching assistant pattern is formed directly on the gate insulating layer.

3. Kim, as indicated above, discloses all the features of the claims except:

Claim 1: an insulating substrate.

a. However, Morozumi discloses:

an insulating substrate (col. 6, ln. 66 – col. 7, ln. 4).

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention to modify the substrate in Kim, with the insulating substrate as taught by Morozumi, because blooming and smear can be avoided.

Response to Arguments

Applicant's arguments filed 5/8/07, pertaining to claims 1-4, have been fully considered but they are not persuasive. The applicant argues that the prior art of record does not

teach or suggest, an etching assistant pattern located out of an area defined by intersections of the gate line and the data line, as in claim 1. The claim language, an etching assistant pattern... and located out of an area defined by intersections of the gate line and the data line, only requires that the etching assistant pattern is located out of the area defined. However, the wording does not preclude the etching assistant pattern from being in the intersection also. Additionally, the applicant is advised that claims in a pending application should be given their broadest reasonable interpretation. *In re Pearson*, 181 USPQ 641 (CCPA 1974).

Conclusion

2. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).


A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Art Unit: 2812

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ron E. Pompey whose telephone number is (571) 272-1680. The examiner can normally be reached on 9AM - 5PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael S. Lebentritt can be reached on (571) 272-1873. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.


Ron Pompey
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8/2/07


MICHAEL LEBENTRITT
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